

# STPS1L40M

## LOW DROP POWER SCHOTTKY RECTIFIER

**Table 1: Main Product Characteristics** 

I <sub>F(AV)</sub>	1 A
V <sub>RRM</sub>	40 V
T <sub>j</sub> (max)	150°C
V <sub>F</sub> (max)	0.40 V

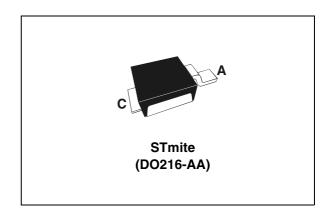
### **FEATURES AND BENEFITS**

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop for higher efficiency and extented battery life
- Low thermal resistance
- Avalanche capability specified

#### **DESCRIPTION**

Single Schottky rectifier suited for switch mode power supplies and high frequency DC to DC converters

Packaged in STmite, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications. Due to the small size of the package this device fits battery powered equipment (cellular, notebook, PDA's, printers) as well chargers and PCMCIA cards.



**Table 2: Order Code** 

Part Number	Marking		
STPS1L40M	1L4		

Table 3: Absolute Ratings (limiting values)

Symbol	Paramete	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage	40	V	
I <sub>F(RMS)</sub>	RMS forward voltage		2	Α
I <sub>F(AV)</sub>	Average forward current $T_c = 140^{\circ}C  \delta = 0.5$		1	Α
I <sub>FSM</sub>	Surge non repetitive forward current 10 ms sinusoidal		50	Α
P <sub>ARM</sub>	Repetitive peak avalanche power	1200	W	
T <sub>stg</sub>	Storage temperature range	-65 to + 150	°C	
T <sub>j</sub>	Maximum operating junction temperatu	150	°C	
dV/dt	Critical rate of rise of reverse voltage (	10000	V/µs	

<sup>\*:</sup>  $\frac{dPtot}{dTj} > \frac{1}{Rth(j-a)}$  thermal runaway condition for a diode on its own heatsink

**Table 4: Thermal Resistance** 

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub> *	Junction to case	20	°C/W
R <sub>th(j-l)</sub> *	Junction to ambient	250	°C/W

<sup>\*</sup> Mounted with minimum recommended pad size, PC board FR4.

**Table 5: Static Electrical Characteristics** 

Symbol	Parameter	Tests conditions		Min.	Тур	Max.	Unit
I <sub>R</sub> * Reverse leakage currer		T <sub>j</sub> = 25°C	$V_R = V_{RRM}$		0.021	0.063	
	Poverse leekage ourrent	T <sub>j</sub> = 85°C			1.3	4.0	mA
	neverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = 20V		0.007	0.021	ША
		T <sub>j</sub> = 85°C			0.49	1.5	
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A		0.40	0.46	
V <sub>F</sub> *		T <sub>j</sub> = 85°C	if - IV		0.35	0.40	V
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 3A		0.52	0.60	V
		T <sub>j</sub> = 85°C	11- 07		0.50	0.58	

Pulse test: \* tp = 380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses use the following equation:  $P = 0.34 \times I_{F(AV)} + 0.07 I_{F}^{2} (RMS)$ 

Figure 1: Conduction losses versus average current

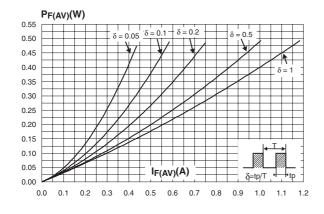


Figure 2: Average forward current versus ambient temperature ( $\delta$  = 0.5)

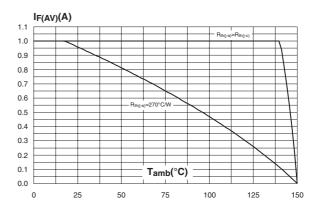


Figure 3: Normalized avalanche power derating versus pulse duration

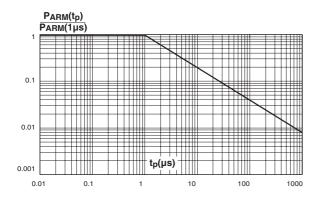


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values)

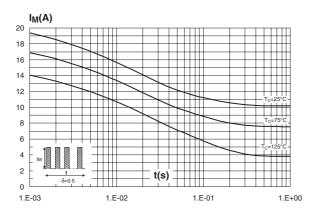


Figure 7: Reverse leakage current versus reverse voltage applied (typical values)

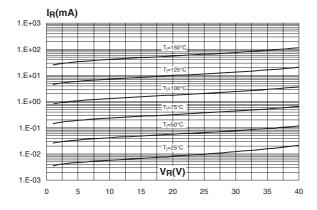


Figure 4: Normalized avalanche power derating versus junction temperature

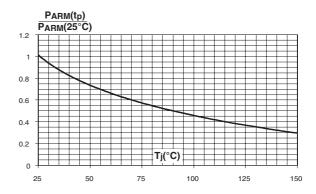


Figure 6: Relative variation of thermal impedance junction to ambient versus pulse duration

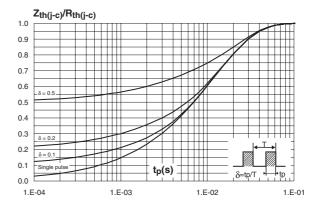
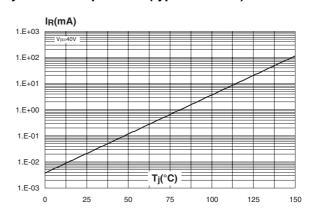


Figure 8: Reverse leakage current versus junction temperature (typical values)



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Figure 9: Junction capacitance versus reverse voltage applied (typical values)

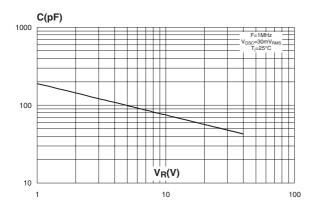


Figure 11: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4,  $Cu=35\mu m$ , typical values)

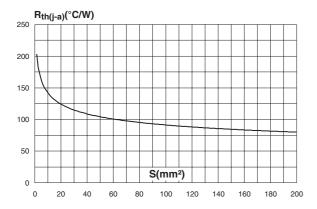
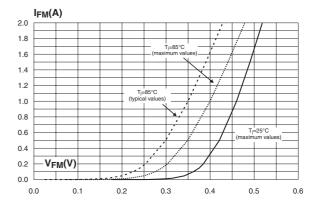
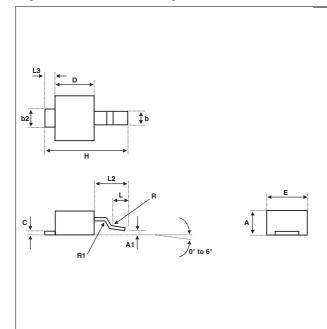


Figure 10: Forward voltage drop versus forward current



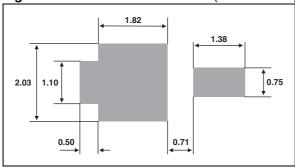
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Figure 12: STmite Package Mechanical Data



	DIMENSIONS					
REF.	. Millimet		ters		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.85	1.00	1.15	0.033	0.039	0.045
A1	-0.05		0.05	-0.002		0.002
b	0.40		0.65	0.016		0.025
b2	0.70		1.00	0.027		0.039
С	0.10		0.25	0.004		0.010
D	1.75	1.90	2.05	0.069	0.007	0.081
Е	1.75	1.90	2.05	0.069	0.007	0.081
Н	3.60	3.75	3.90	0.142	0.148	0.154
L	0.50	0.63	0.80	0.020	0.025	0.031
L2	1.20	1.35	1.50	0.047	0.053	0.059
L3		0.50			0.019	
		ref			ref	
R	0.07			0.003		
R1	0.07			0.003		

Figure 13: Foot Print Dimensions (in millimeters)



**Table 6: Ordering Information** 

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS1L40M	1L4	STmite	15.5 mg	12000	Tape & reel

**Table 7: Revision History** 

Date	Revision	Description of Changes
Jul-2003	2A	Last update.
13-Sep-2004	3	STmite package dimensions reference A1 change: from blank (min) to -0.05mm and from 0.10 (max) to 0.05mm.

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